

Low Noise Dual Operational Amplifier

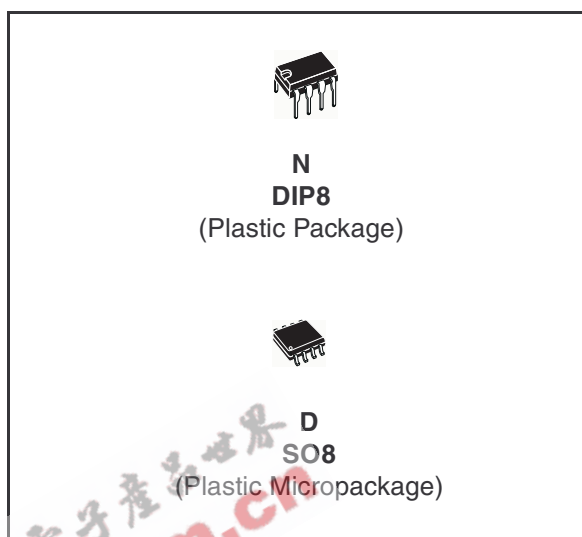
- Low voltage noise: **4.5nV/√Hz**
- High gain bandwidth product: **15MHz**
- High slew rate: **7V/μs**
- Low distortion: 0.002%
- Excellent frequency stability
- ESD protection 2kV

Description

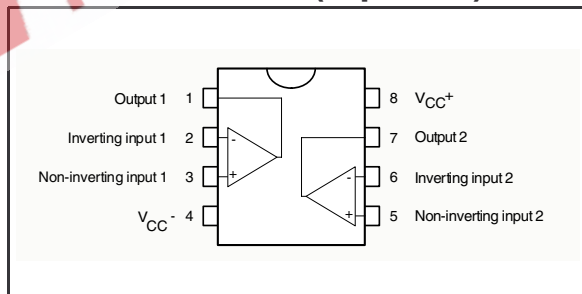
The LM833 is a monolithic dual operational amplifier particularly well suited for audio applications.

It offers low voltage noise (4.5nV/√Hz) and high frequency performances (15MHz Gain Bandwidth product, 7V/μs slew rate).

In addition the LM833 has also a very low distortion (0.002%) and excellent phase/gain margins.



Pin Connections (top view)



Order Codes

| Part Number | Temperature Range | Package | Packaging | Marking |
|-------------|-------------------|-------------------------------|---------------------|---------|
| LM833N | -40, +105°C | DIP8 | Tube | LM833N |
| LM833D/DT | | S8-8 | Tube or Tape & Reel | 833 |
| LM833YD/YDT | -40, +125°C | SO-8 (automotive grade level) | Tube or Tape & Reel | 833Y |

1 Absolute Maximum Ratings

Table 1. Key parameters and their absolute maximum ratings

| Symbol | Parameter | Value | Unit |
|-------------------|---------------------------------------|-------------|------|
| V _{CC} | Supply Voltage | ±18 or +36 | V |
| V _{id} | Differential Input Voltage - note (1) | ±30 | V |
| V _i | Input Voltage - see note 1 | ±15 | V |
| | Output Short Circuit Duration | Infinite | s |
| T _{oper} | Operating Free-Air Temperature Range | -40 to 105 | °C |
| T _j | Junction Temperature | +150 | °C |
| T _{stg} | Storage Temperature | -65 to +150 | °C |
| P _{tot} | Maximum Power Dissipation - note (2) | 500 | mW |
| ESD | HBM: Human Body Model(3) | 2 | kV |
| | MM: Machine Model(4) | 200 | V |
| | CDM: Charged Device Model | 1500 | V |

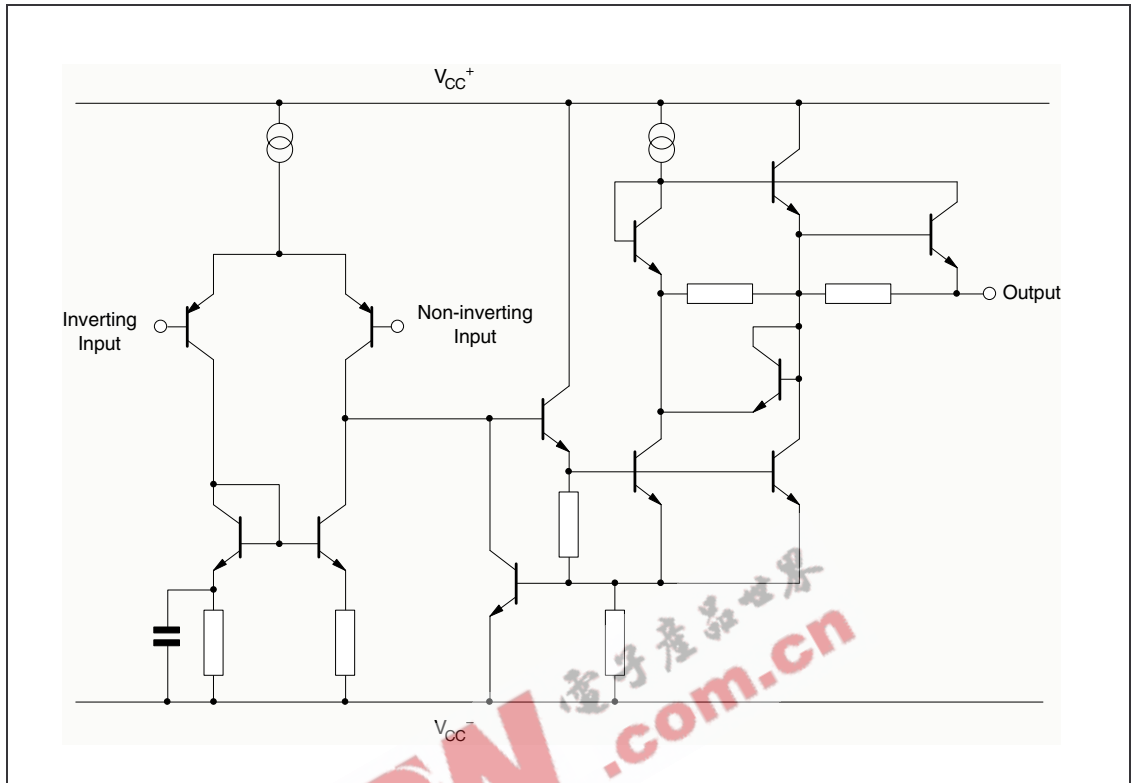
1. Either or both input voltages must not exceed the magnitude of V_{CC} or V_{CC}.
2. Power dissipation must be considered to ensure maximum junction temperature (T_j) is not exceeded.
3. Human body model, 100pF discharged through a 1.5kΩ resistor into pin of device.
4. Machine model ESD, a 200pF cap is charged to the specified voltage, then discharged directly into the IC with no external series resistor (internal resistor < 5Ω), into pin to pin of device.

Table 2. Operating conditions

| Symbol | Parameter | Value | Unit |
|-----------------|----------------|-------------|------|
| V _{CC} | Supply Voltage | ±2.5 to ±15 | V |

2 Typical Application Schematics

Figure 1. Schematic diagram (1/2 LM833)



3 Electrical Characteristics

Table 3. $V_{CC}^+ = +15V$, $V_{CC}^- = -15V$, $T_{amb} = 25^\circ C$ (unless otherwise specified)

| Symbol | Parameter | Min. | Typ. | Max. | Unit |
|-----------------|--|----------|------------------------------|------------|------------------------|
| V_{io} | Input Offset Voltage ($R_s = 10\Omega$, $V_o = 0V$, $V_{ic} = 0V$) | | 0.3 | 5 | mV |
| DV_{io} | Input Offset Voltage Drift $R_s = 10\Omega$, $V_o = 0V$, $T_{min} \leq T_{amb} \leq T_{max}$. | | 2 | | $\mu V/^\circ C$ |
| I_{io} | Input Offset Current ($V_o = 0V$, $V_{ic} = 0V$) | | 25 | 200 | nA |
| I_{ib} | Input Bias Current ($V_o = 0V$, $V_{ic} = 0V$) | | 300 | 1000 | nA |
| V_{icm} | Input Common Mode Voltage Range | ± 12 | ± 14 | | V |
| A_{vd} | Large Signal Voltage Gain ($R_L = 2k\Omega$, $V_o = \pm 10V$) | 90 | 100 | | dB |
| $\pm V_{opp}$ | Output Voltage Swing ($V_{id} = \pm 1V$) $R_L = 2.0k\Omega$ $R_L = 2.0k\Omega$ $R_L = 10k\Omega$ $R_L = 10k\Omega$ | 10 12 | 13.7 -14 13.9 -14.4 | -10 -12 | V |
| CMR | Common-mode Rejection Ratio ($V_{ic} = \pm 13V$) | 80 | 100 | | dB |
| SVR | Supply Voltage Rejection Ratio ($V_{CC}^+ / V_{CC}^- = +15V / -15V$ to $+5V / -5V$) | 80 | 105 | | dB |
| I_{CC} | Supply Current ($V_o = 0V$, All amplifiers) | | 4 | 8 | mA |
| SR | Slew Rate ($V_i = -10V$ to $+10V$, $R_L = 2k\Omega$, $A_V = +1$) | 5 | 7 | | V/ μs |
| GBP | Gain Bandwidth Product ($R_L = 2k\Omega$, $C_L = 100pF$, $f = 100kHz$) | 10 | 15 | | MHz |
| B | Unity Gain Bandwidth (Open loop) | | 9 | | MHz |
| ϕ_m | Phase Margin ($R_L = 2k\Omega$) | | 60 | | Degrees |
| e_n | Equivalent Input Noise Voltage ($R_S = 100\Omega$, $f = 1kHz$) | | 4.5 | | $\frac{nV}{\sqrt{Hz}}$ |
| i_n | Equivalent Input Noise Current ($f = 1kHz$) | | 0.5 | | $\frac{pA}{\sqrt{Hz}}$ |
| THD | Total Harmonic Distortion ($R_L = 2k\Omega$, $f = 20Hz$ to $20kHz$, $V_o = 3V_{rms}$, $A_V = +1$) | | 0.002 | | % |
| V_{O1}/V_{O2} | Channel Separation ($f = 20Hz$ to $20kHz$) | | 120 | | dB |
| FPB | Full Power Bandwidth ($V_o = 27V_{pp}$, $R_L = 2k\Omega$, $THD \leq 1\%$) | | 120 | | kHz |

Figure 2. Total supply current vs. supply voltage

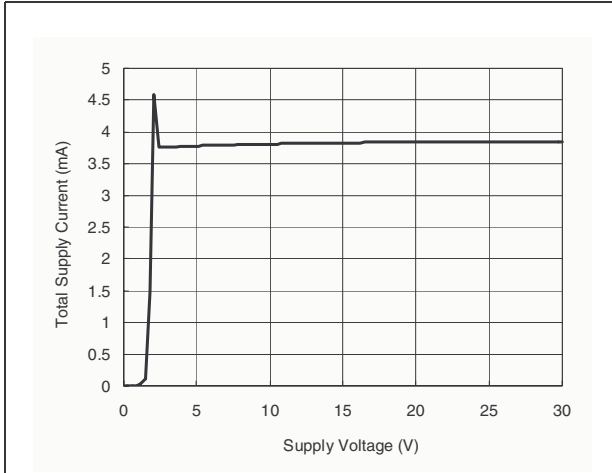


Figure 3. Output voltage vs. supply voltage

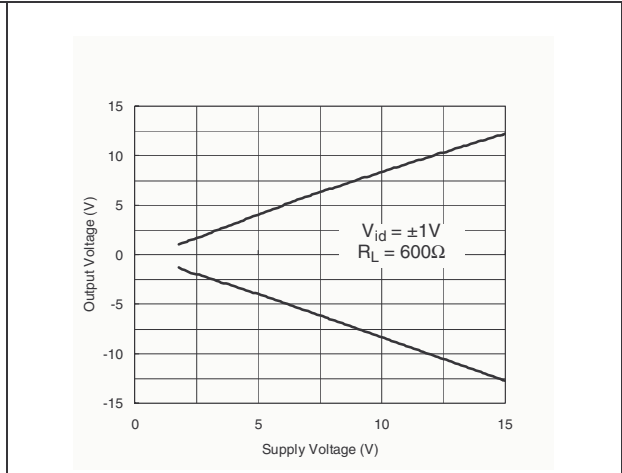


Figure 4. Equivalent input noise voltage vs. frequency

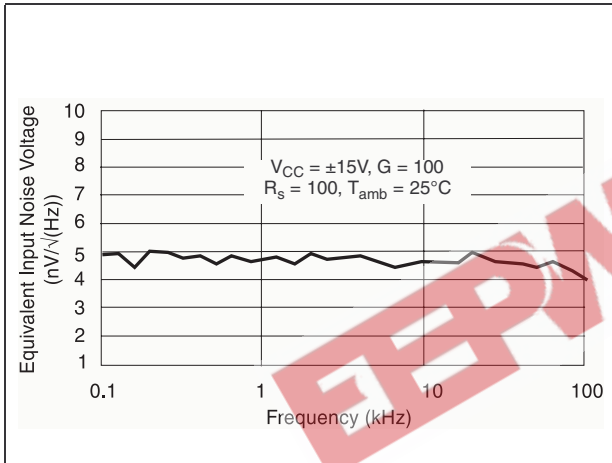


Figure 5. Output short circuit current vs. output voltage

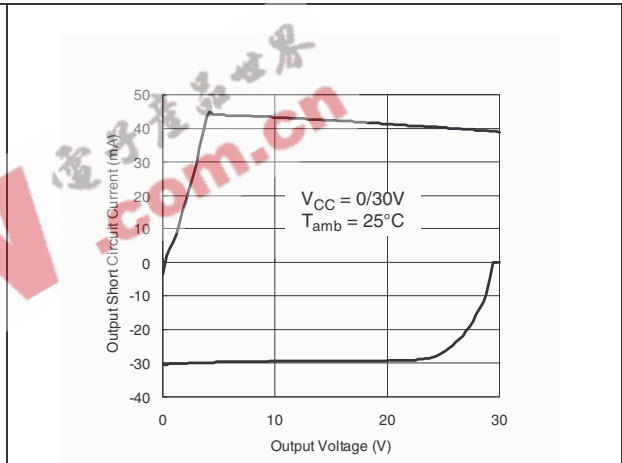


Figure 6. Output voltage vs. supply voltage

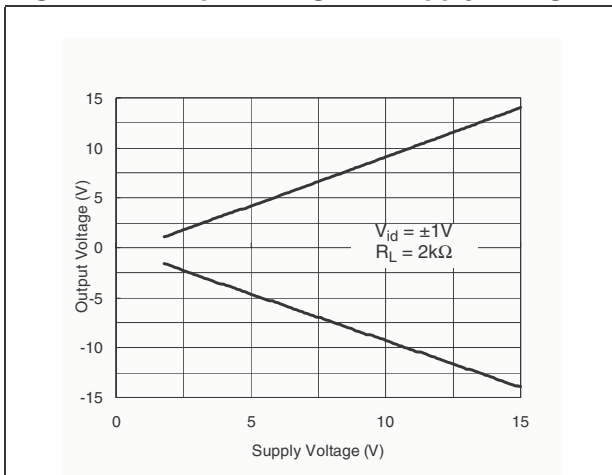


Figure 7. THD+ noise vs. frequency

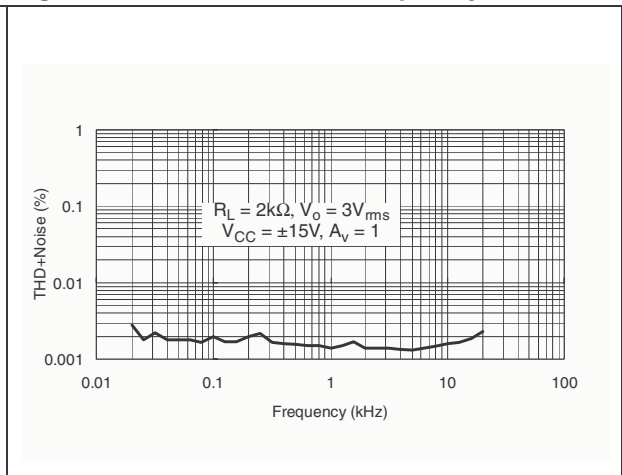


Figure 8. Voltage gain and phase vs. frequency

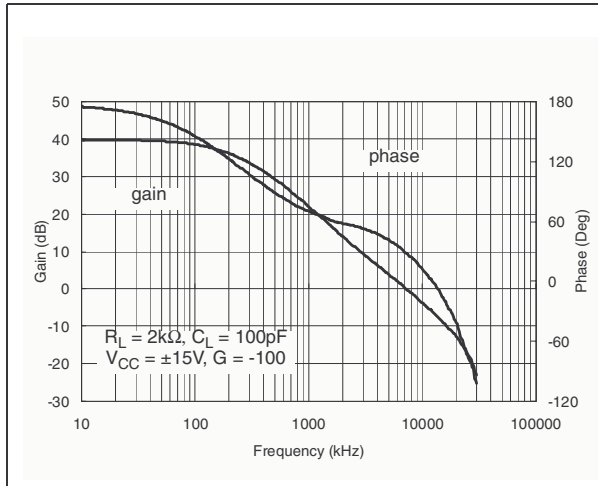
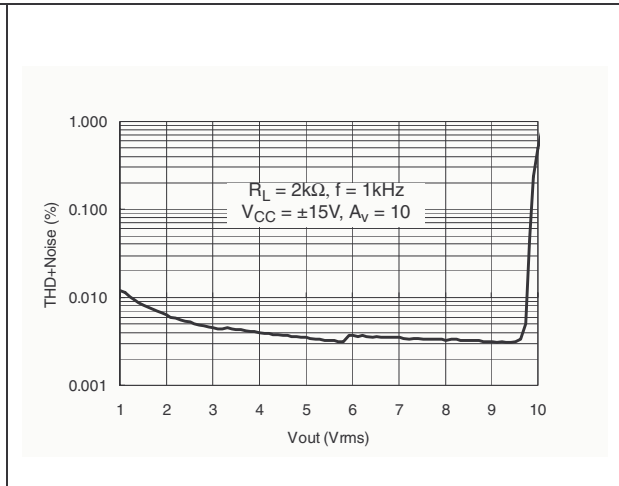


Figure 9. THD + noise vs. Vout

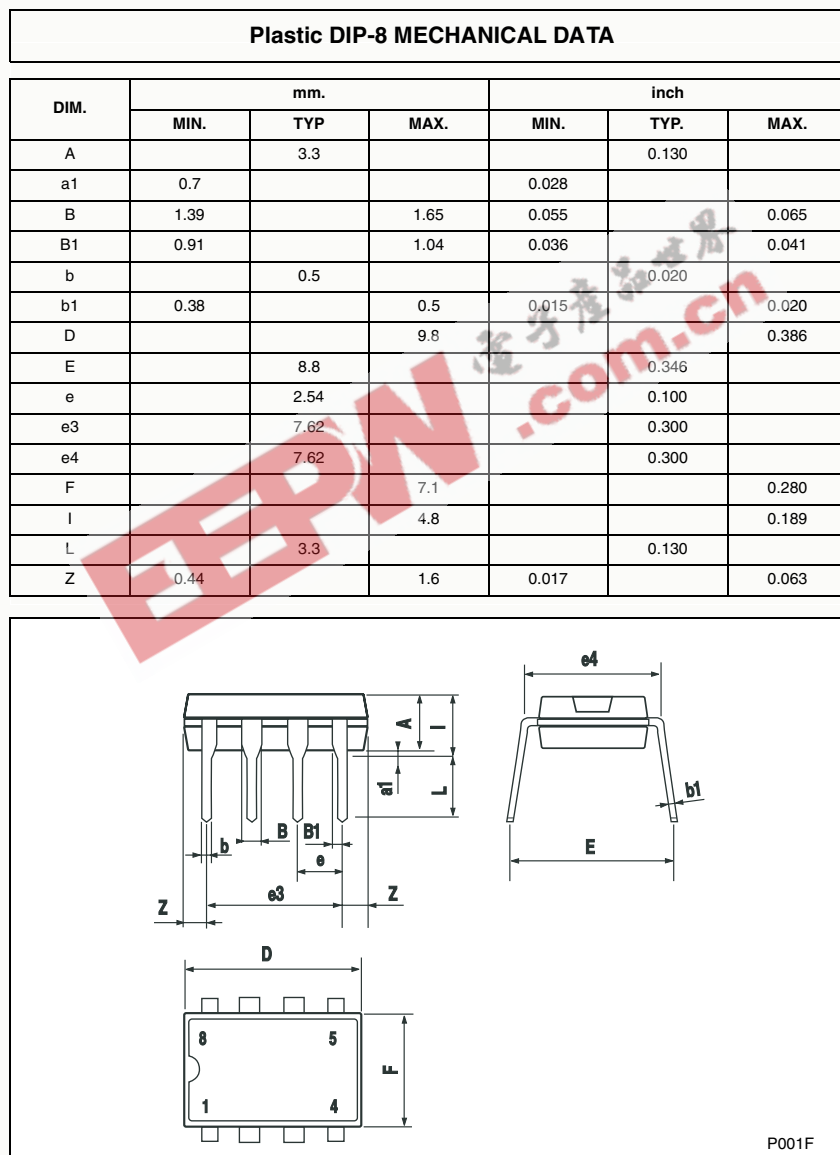


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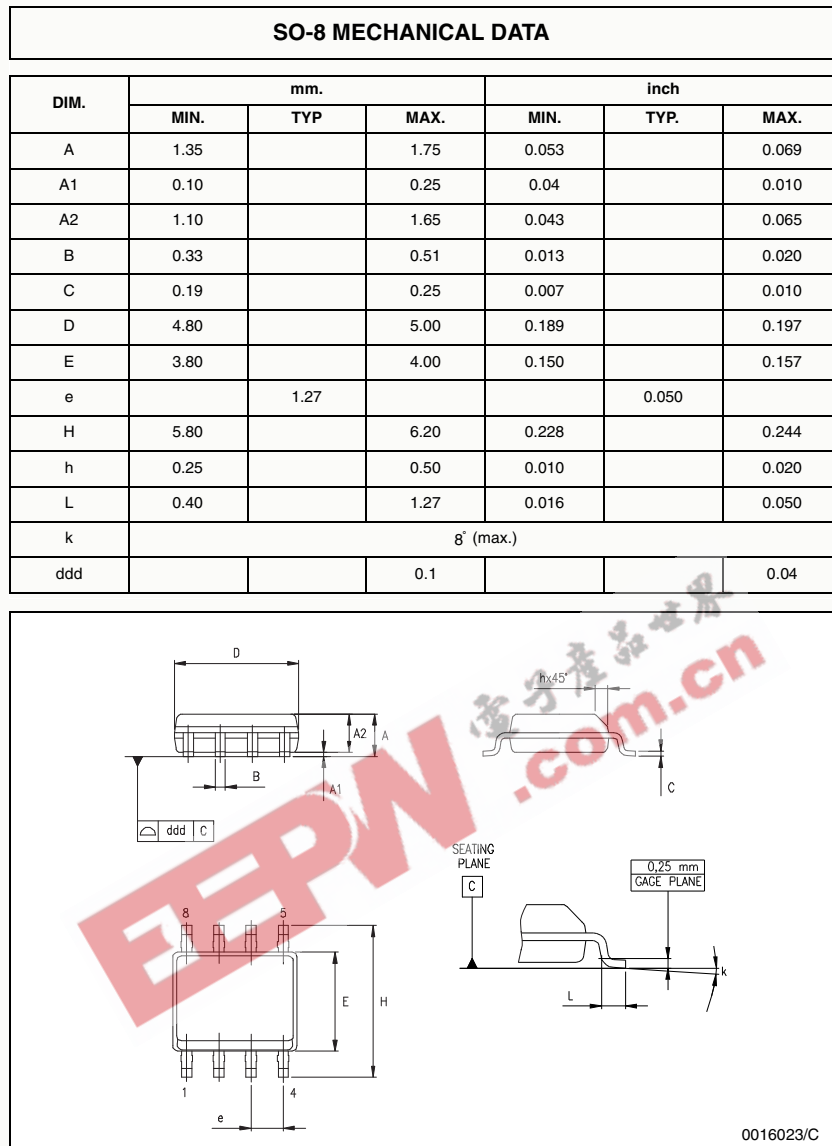
4 Package Mechanical Data

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect. The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: www.st.com.

4.1 DIP-8 Package



4.2 SO-8 Package



5 Revision History

| Date | Revision | Changes |
|-----------|----------|---|
| Nov. 2001 | 1 | Initial release. |
| July 2005 | 2 | 1 - PPAP references inserted in the datasheet see <i>Table on page 1</i> . 2 - ESD protection inserted in <i>Table 1 on page 2</i> |

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